

NTP75N06, NTB75N06

Power MOSFET 75 Amps, 60 Volts N-Channel TO-220 and D²PAK

Designed for low voltage, high speed switching applications in power supplies, converters and power motor controls and bridge circuits.

Typical Applications

- Power Supplies
- Converters
- Power Motor Controls
- Bridge Circuits

MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

| Rating | Symbol | Value | Unit |
|---|--------------------------------------|-------------|------|
| Drain-to-Source Voltage | V _{DSS} | 60 | Vdc |
| Drain-to-Gate Voltage (R _{GS} = 10 MΩ) | V _{DGR} | 60 | Vdc |
| Gate-to-Source Voltage | V _{GS} | ±20 | Vdc |
| - Continuous | V _{GS} | ±30 | |
| - Non-Repetitive (t _p ≤ 10 ms) | | | |
| Drain Current | I _D | 75 | Adc |
| - Continuous @ T _A = 25°C | I _D | 50 | |
| - Continuous @ T _A = 100°C | I _{DM} | 225 | Apk |
| - Single Pulse (t _p ≤ 10 μs) | | | |
| Total Power Dissipation @ T _A = 25°C | P _D | 214 | W |
| Derate above 25°C | | 1.4 | W/°C |
| Total Power Dissipation @ T _A = 25°C | | 2.4 | W |
| Operating and Storage Temperature Range | T _J , T _{stg} | -55 to +175 | °C |
| Single Pulse Drain-to-Source Avalanche Energy - Starting T _J = 25°C (V _{DD} = 50 Vdc, V _{GS} = 10 Vdc, L = 0.3 mH I _{L(pk)} = 75 A, V _{DS} = 60 Vdc) | E _{AS} | 844 | mJ |
| Thermal Resistance | R _{θJC} R _{θJA} | 0.7 62.5 | °C/W |
| - Junction-to-Case | | | |
| - Junction-to-Ambient | | | |
| Maximum Lead Temperature for Soldering Purposes, 1/8" from case for 10 seconds | T _L | 260 | °C |

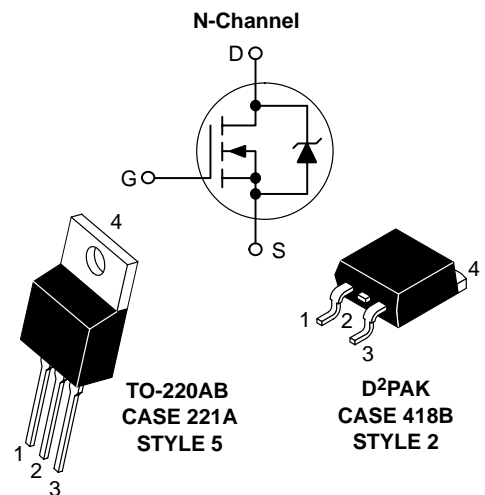


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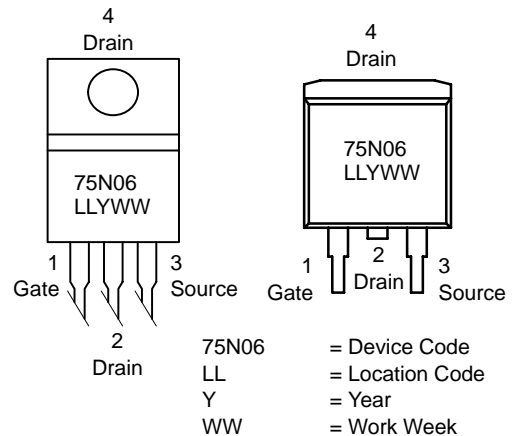
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**75 AMPERES
60 VOLTS**

R_{DS(on)} = 9.5 mΩ



MARKING DIAGRAMS & PIN ASSIGNMENTS



ORDERING INFORMATION

| Device | Package | Shipping |
|------------|--------------------|-----------------|
| NTP75N06 | TO-220AB | 50 Units/Rail |
| NTB75N06 | D ² PAK | 50 Units/Rail |
| NTB75N06T4 | D ² PAK | 800/Tape & Reel |

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ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

| Characteristic | Symbol | Min | Typ | Max | Unit |
|----------------|--------|-----|-----|-----|------|
|----------------|--------|-----|-----|-----|------|

OFF CHARACTERISTICS

| | | | | | |
|---|----------------------|---------|----------|-----------|--------------|
| Drain-to-Source Breakdown Voltage (Note 1) (V _{GS} = 0 Vdc, I _D = 250 μAdc) Temperature Coefficient (Positive) | V _{(BR)DSS} | 60 - | 71 73 | - - | Vdc mV/°C |
| Zero Gate Voltage Drain Current (V _{DS} = 60 Vdc, V _{GS} = 0 Vdc) (V _{DS} = 60 Vdc, V _{GS} = 0 Vdc, T _J = 150°C) | I _{DSS} | - - | - - | 10 100 | μAdc |
| Gate-Body Leakage Current (V _{GS} = ±20 Vdc, V _{DS} = 0 Vdc) | I _{GSS} | - | - | ±100 | nAdc |

ON CHARACTERISTICS (Note 1)

| | | | | | |
|--|---------------------|----------|--------------|-----------|--------------|
| Gate Threshold Voltage (Note 1) (V _{DS} = V _{GS} , I _D = 250 μAdc) Threshold Temperature Coefficient (Negative) | V _{GS(th)} | 2.0 - | 2.8 8.0 | 4.0 - | Vdc mV/°C |
| Static Drain-to-Source On-Resistance (Note 1) (V _{GS} = 10 Vdc, I _D = 37.5 Adc) | R _{DS(on)} | - | 8.2 | 9.5 | mOhm |
| Static Drain-to-Source On-Voltage (Note 1) (V _{GS} = 10 Vdc, I _D = 75 Adc) (V _{GS} = 10 Vdc, I _D = 37.5 Adc, T _J = 150°C) | V _{DS(on)} | - - | 0.72 0.63 | 0.86 - | Vdc |
| Forward Transconductance (Note 1) (V _{DS} = 15 Vdc, I _D = 37.5 Adc) | g _{FS} | - | 40.2 | - | mhos |

DYNAMIC CHARACTERISTICS

| | | | | | | |
|----------------------|---|------------------|---|------|------|----|
| Input Capacitance | (V _{DS} = 25 Vdc, V _{GS} = 0 Vdc, f = 1.0 MHz) | C _{iss} | - | 3220 | 4510 | pF |
| Output Capacitance | | C _{oss} | - | 1020 | 1430 | |
| Transfer Capacitance | | C _{rss} | - | 234 | 330 | |

SWITCHING CHARACTERISTICS (Note 2)

| | | | | | | |
|---------------------|---|---------------------|---|-----|-----|----|
| Turn-On Delay Time | (V _{DD} = 30 Vdc, I _D = 75 Adc, V _{GS} = 10 Vdc, R _G = 9.1 Ω) (Note 1) | t _{d(on)} | - | 16 | 25 | ns |
| Rise Time | | t _r | - | 112 | 155 | |
| Turn-Off Delay Time | | t _{d(off)} | - | 90 | 125 | |
| Fall Time | | t _f | - | 100 | 140 | |
| Gate Charge | (V _{DS} = 48 Vdc, I _D = 75 Adc, V _{GS} = 10 Vdc) (Note 1) | Q _T | - | 92 | 130 | nC |
| | | Q ₁ | - | 14 | - | |
| | | Q ₂ | - | 44 | - | |

SOURCE-DRAIN DIODE CHARACTERISTICS

| | | | | | | |
|--------------------------------|---|-----------------|--------|------------|----------|-----|
| Forward On-Voltage | (I _S = 75 Adc, V _{GS} = 0 Vdc) (Note 1) (I _S = 75 Adc, V _{GS} = 0 Vdc, T _J = 150°C) | V _{SD} | - - | 1.0 0.9 | 1.1 - | Vdc |
| Reverse Recovery Time | (I _S = 75 Adc, V _{GS} = 0 Vdc, di _S /dt = 100 A/μs) (Note 1) | t _{rr} | - | 77 | - | ns |
| | | t _a | - | 49 | - | |
| | | t _b | - | 28 | - | |
| Reverse Recovery Stored Charge | | Q _{RR} | - | 0.16 | - | μC |

1. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2%.
2. Switching characteristics are independent of operating junction temperatures.

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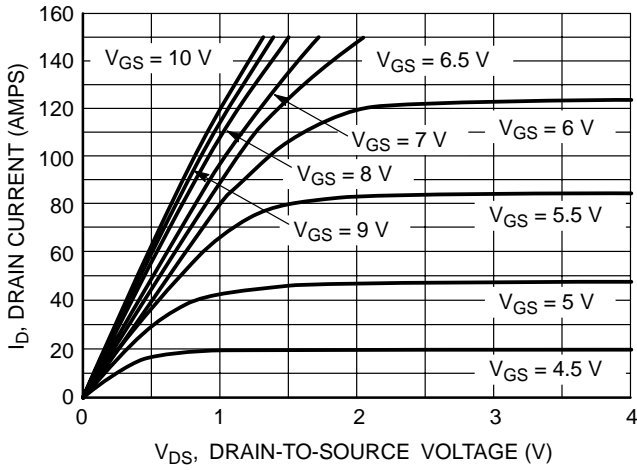


Figure 1. On-Region Characteristics

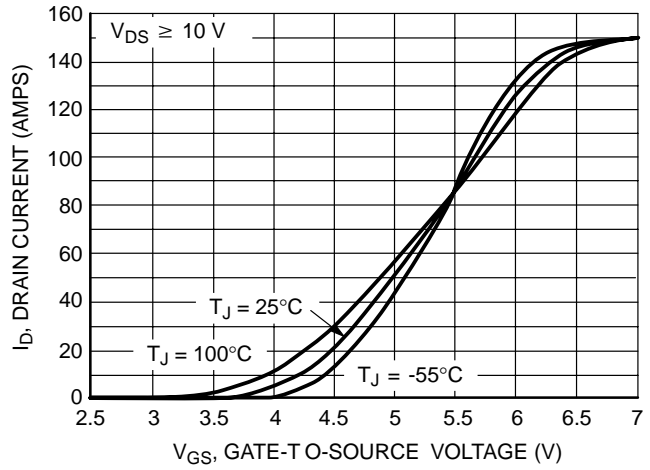


Figure 2. Transfer Characteristics

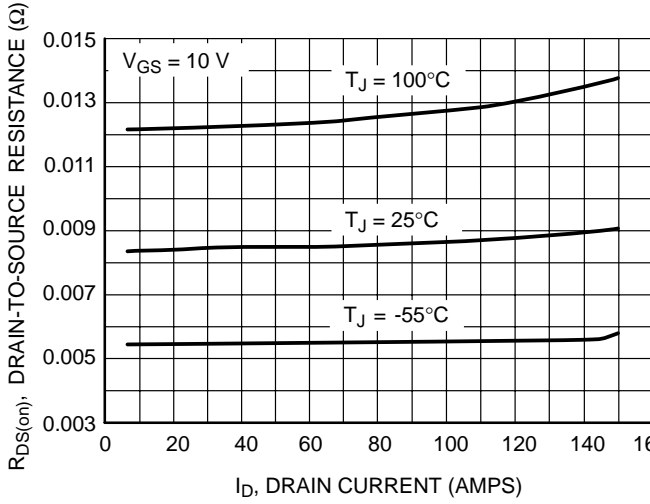


Figure 3. On-Resistance vs. Gate-to-Source Voltage

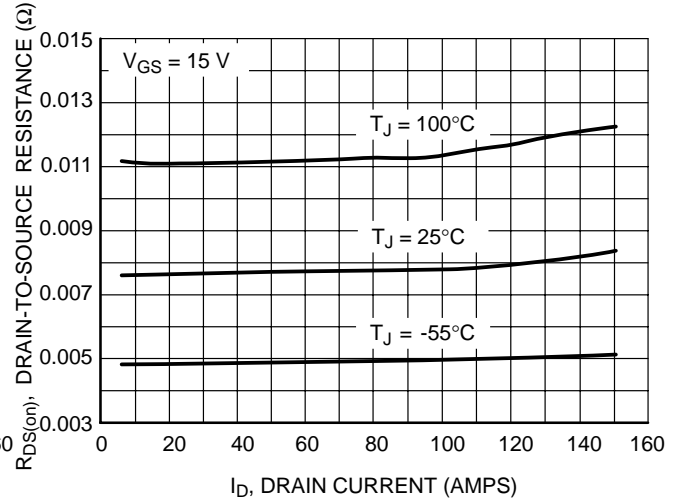


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

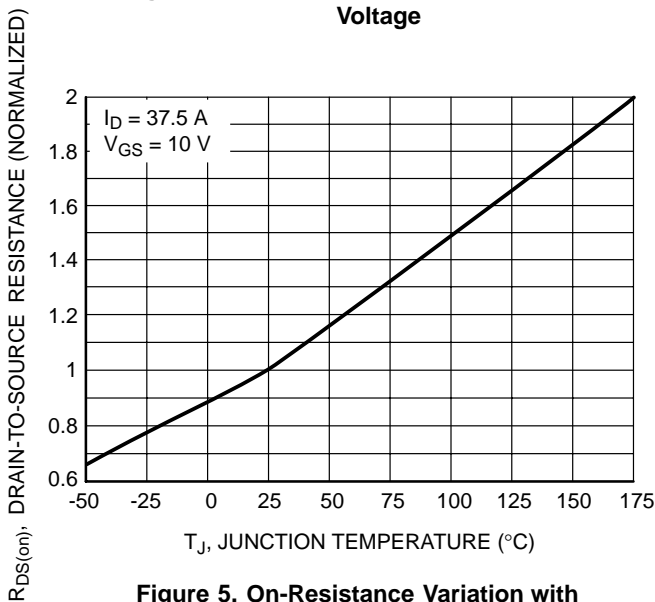


Figure 5. On-Resistance Variation with Temperature

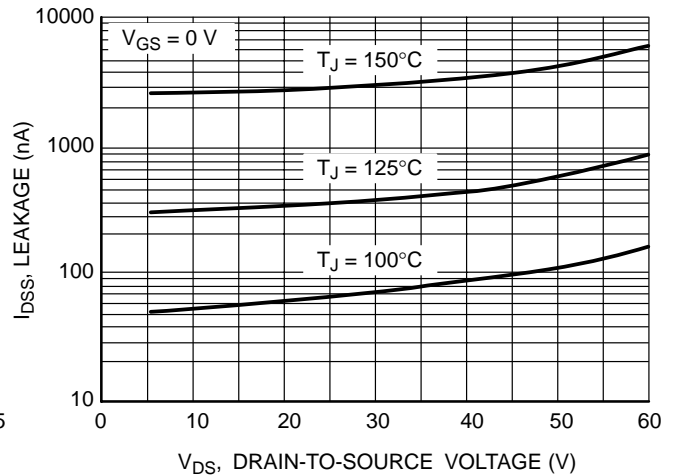


Figure 6. Drain-to-Source Leakage Current vs. Voltage

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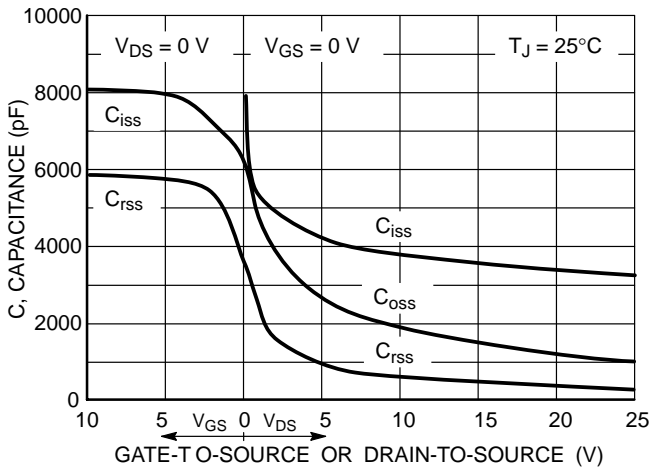


Figure 7. Capacitance Variation

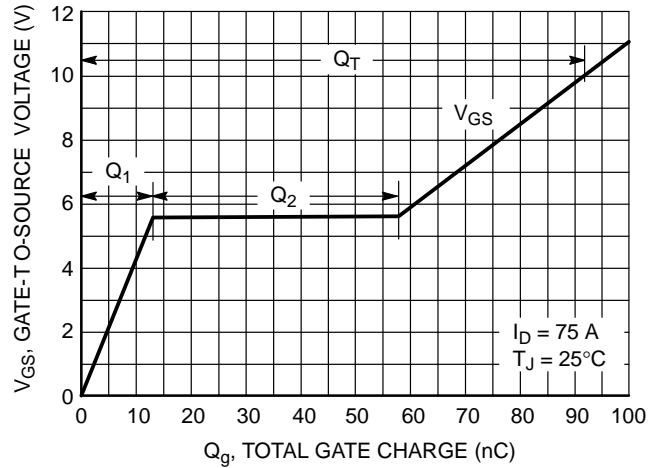


Figure 8. Gate-to-Source and Drain-to-Source Voltage vs. Total Charge

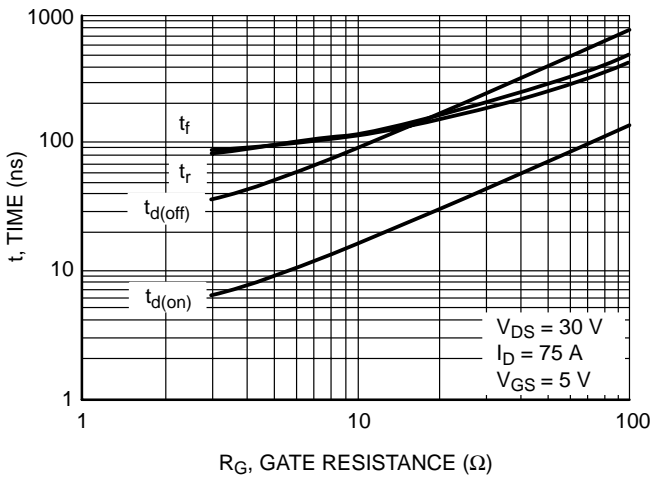


Figure 9. Resistive Switching Time Variations vs. Gate Resistance

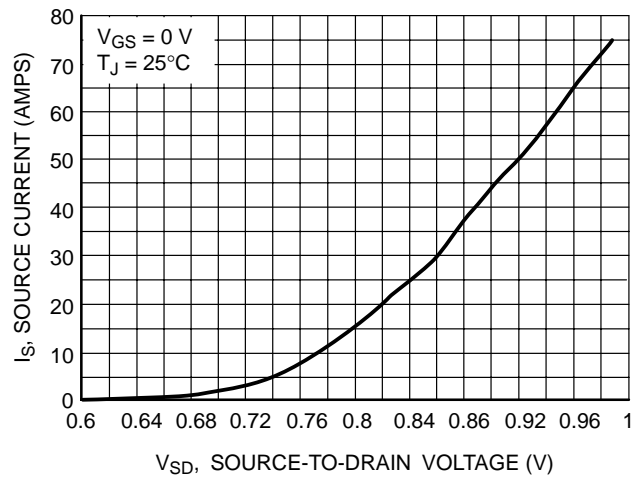


Figure 10. Diode Forward Voltage vs. Current

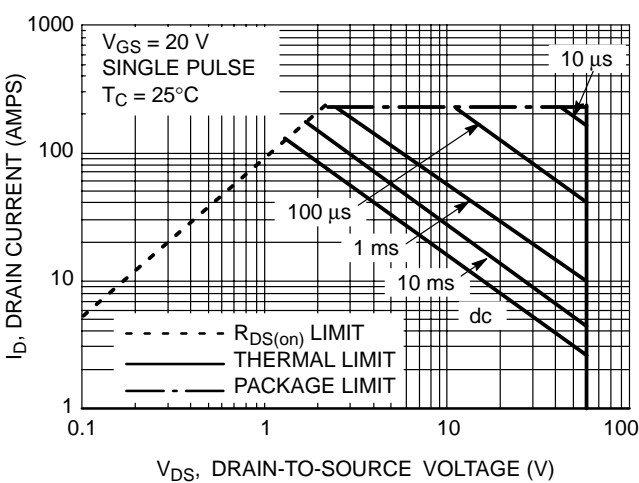


Figure 11. Maximum Rated Forward Biased Safe Operating Area

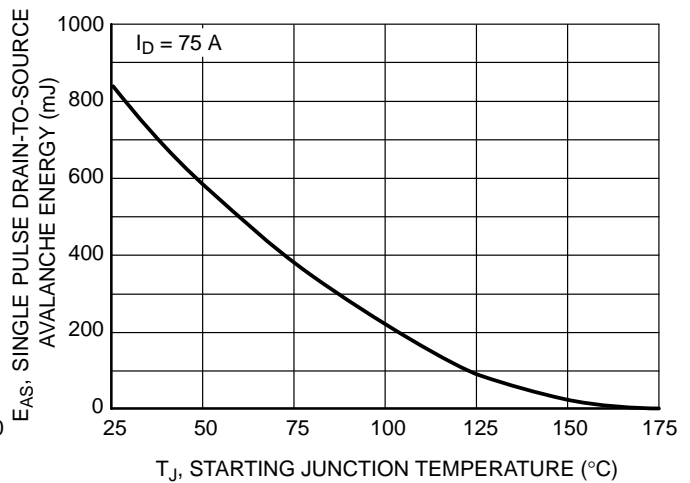


Figure 12. Maximum Avalanche Energy vs. Starting Junction Temperature

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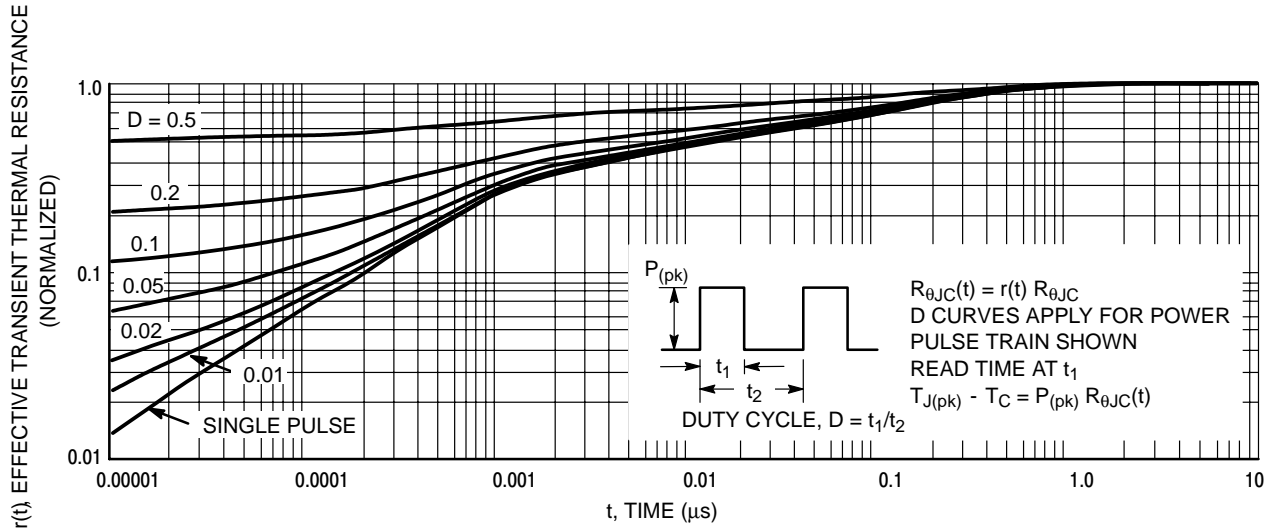
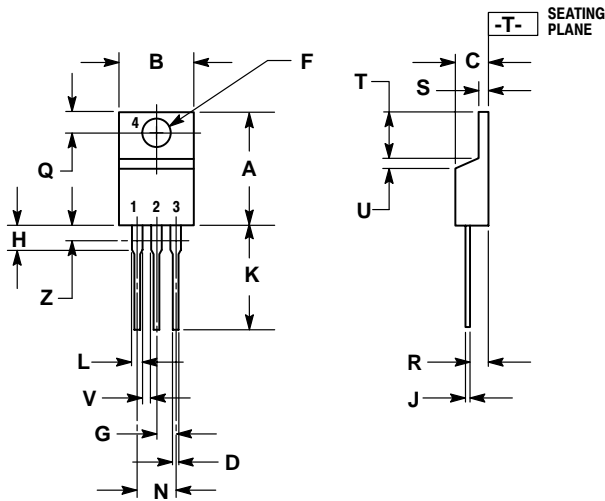


Figure 13. Thermal Response

PACKAGE DIMENSIONS

TO-220 THREE-LEAD
TO-220AB
CASE 221A-09
ISSUE AA



- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

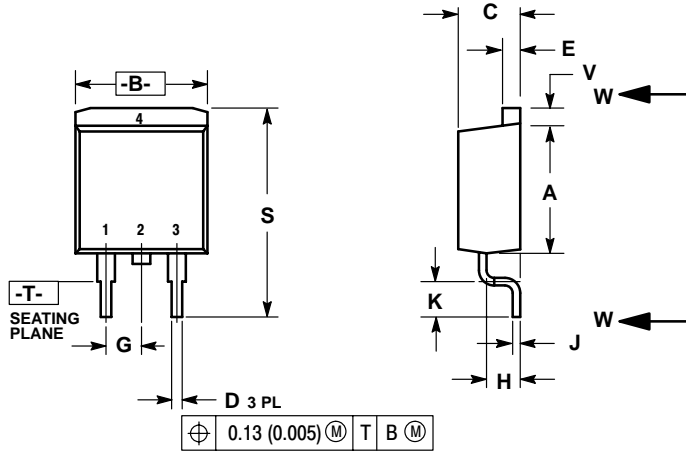
| DIM | INCHES | | MILLIMETERS | |
|-----|--------|-------|-------------|-------|
| | MIN | MAX | MIN | MAX |
| A | 0.570 | 0.620 | 14.48 | 15.75 |
| B | 0.380 | 0.405 | 9.66 | 10.28 |
| C | 0.160 | 0.190 | 4.07 | 4.82 |
| D | 0.025 | 0.035 | 0.64 | 0.88 |
| F | 0.142 | 0.147 | 3.61 | 3.73 |
| G | 0.095 | 0.105 | 2.42 | 2.66 |
| H | 0.110 | 0.155 | 2.80 | 3.93 |
| J | 0.018 | 0.025 | 0.46 | 0.64 |
| K | 0.500 | 0.562 | 12.70 | 14.27 |
| L | 0.045 | 0.060 | 1.15 | 1.52 |
| N | 0.190 | 0.210 | 4.83 | 5.33 |
| Q | 0.100 | 0.120 | 2.54 | 3.04 |
| R | 0.080 | 0.110 | 2.04 | 2.79 |
| S | 0.045 | 0.055 | 1.15 | 1.39 |
| T | 0.235 | 0.255 | 5.97 | 6.47 |
| U | 0.000 | 0.050 | 0.00 | 1.27 |
| V | 0.045 | --- | 1.15 | --- |
| Z | --- | 0.080 | --- | 2.04 |

- STYLE 5:
PIN 1. GATE
2. DRAIN
3. SOURCE
4. DRAIN

NTP75N06, NTB75N06

PACKAGE DIMENSIONS

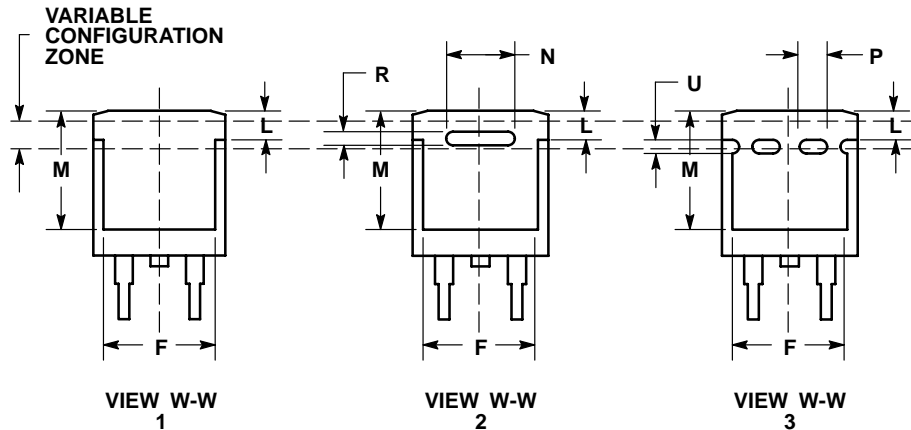
D²PAK
CASE 418B-04
ISSUE H



- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. 418B-01 THRU 418B-03 OBSOLETE, NEW STANDARD 418B-04.

| DIM | INCHES | | MILLIMETERS | |
|-----|-----------|-------|-------------|-------|
| | MIN | MAX | MIN | MAX |
| A | 0.340 | 0.380 | 8.64 | 9.65 |
| B | 0.380 | 0.405 | 9.65 | 10.29 |
| C | 0.160 | 0.190 | 4.06 | 4.83 |
| D | 0.020 | 0.035 | 0.51 | 0.89 |
| E | 0.045 | 0.055 | 1.14 | 1.40 |
| F | 0.310 | 0.350 | 7.87 | 8.89 |
| G | 0.100 BSC | | 2.54 BSC | |
| H | 0.080 | 0.110 | 2.03 | 2.79 |
| J | 0.018 | 0.025 | 0.46 | 0.64 |
| K | 0.090 | 0.110 | 2.29 | 2.79 |
| L | 0.052 | 0.072 | 1.32 | 1.83 |
| M | 0.280 | 0.320 | 7.11 | 8.13 |
| N | 0.197 REF | | 5.00 REF | |
| P | 0.079 REF | | 2.00 REF | |
| R | 0.039 REF | | 0.99 REF | |
| S | 0.575 | 0.625 | 14.60 | 15.88 |
| V | 0.045 | 0.055 | 1.14 | 1.40 |

- STYLE 2:
PIN 1. GATE
2. DRAIN
3. SOURCE
4. DRAIN



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